

General Purpose Transistors

NPN Silicon

2N3903, 2N3904

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

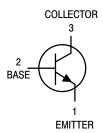
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

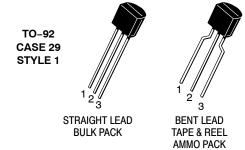
THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

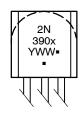
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates Data in addition to JEDEC Requirements.





MARKING DIAGRAMS



x = 3 or 4
 Y = Year
 WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N3903, 2N3904

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

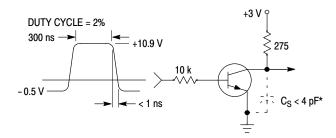
	Characteristic		Symbol	Min	Max	Unit
OFF CHARACTER	RISTICS			•		•
Collector – Emitter	Breakdown Voltage (Note 2) (I _C = 1.0 mAdc, I _B = 0)		V _{(BR)CEO}	40	-	Vdc
Collector - Base Br	reakdown Voltage (I _C = 10 μAdc, I _E = 0)		V _{(BR)CBO}	60	-	Vdc
Emitter - Base Brea	akdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Currer	nt (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	-	50	nAdc
Collector Cutoff Cu	urrent (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERI	STICS	-		•	•	•
DC Current Gain (I (I _C = 0.1 mAdc, V _C		2N3903	h _{FE}	20	_	-
$(I_C = 1.0 \text{ mAdc}, V_C)$	_{CE} = 1.0 Vdc)	2N3904 2N3903 2N3904		40 35 70	- - -	
$(I_C = 10 \text{ mAdc}, V_{CI})$	_E = 1.0 Vdc)	2N3903		50	150	
$(I_C = 50 \text{ mAdc}, V_{CI})$	_E = 1.0 Vdc)	2N3904 2N3903		100 30	300	
(I _C = 100 mAdc, V ₀	_{CE} = 1.0 Vdc)	2N3904 2N3903		60 15	_ _	
		2N3904		30	_	
Collector – Emitter $(I_C = 10 \text{ mAdc}, I_B = (I_C = 50 \text{ mAdc}, I_B = 10 \text{ mAdc})$			V _{CE(sat)}	_ _	0.2 0.3	Vdc
Base – Emitter Satu (I _C = 10 mAdc, I _B = (I _C = 50 mAdc, I _B =	V _{BE(sat)}	0.65	0.85 0.95	Vdc		
SMALL-SIGNAL	CHARACTERISTICS	I		I	1	I
Current - Gain - Ba	andwidth Product		f _T			MHz
(I _C = 10 mAdc, V _{CI}	E = 20 Vdc, f = 100 MHz)	2N3903 2N3904		250 300	_ _	
Output Capacitano	ee ($V_{CB} = 5.0 \text{ Vdc}$, $I_{E} = 0$, $f = 1.0 \text{ MHz}$)		C_{obo}	_	4.0	pF
Input Capacitance	$(V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C_{ibo}	-	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _C	_{DE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback (I _C = 1.0 mAdc, V _C	Ratio _{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻⁴
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)			h _{fe}	50 100	200 400	-
Output Admittance	e (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (I _C = 100 μAdc, V _C	_{CE} = 5.0 Vdc, R _S = 1.0 k Ω, f = 1.0 kHz)	2N3903 2N3904	NF	_ _	6.0 5.0	dB
SWITCHING CHAI	RACTERISTICS			1	1	1
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	_	35	ns
Rise Time	$I_{C} = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$	-	t _r	_	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t _s	_ _ _	175 200	ns
Fall Time		-	t _f	_	50	ns

^{2.} Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

ORDERING INFORMATION

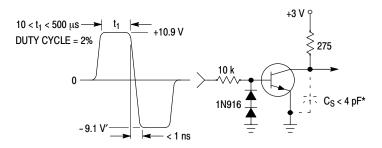
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

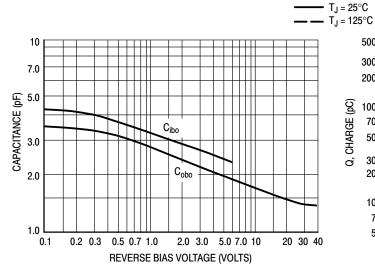


* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

2N3903, 2N3904

TYPICAL TRANSIENT CHARACTERISTICS



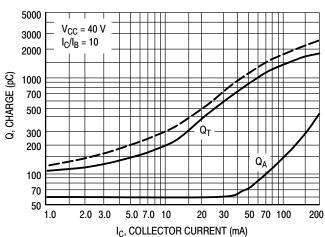
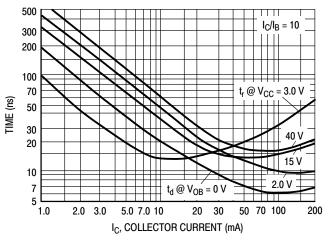


Figure 3. Capacitance

Figure 4. Charge Data



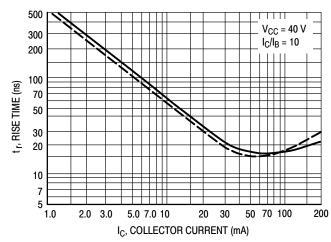
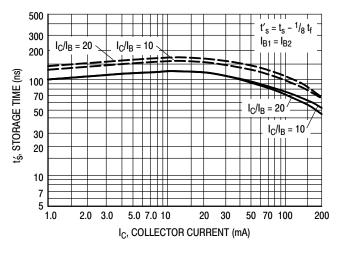


Figure 5. Turn - On Time

Figure 6. Rise Time



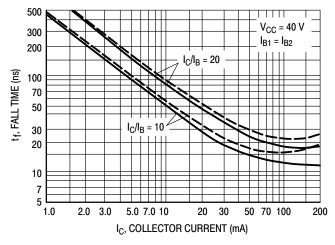
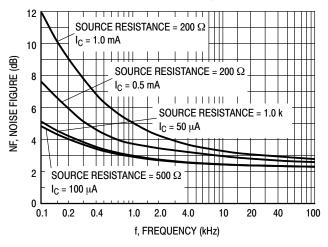


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



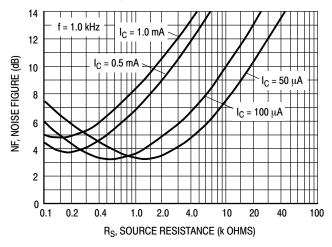
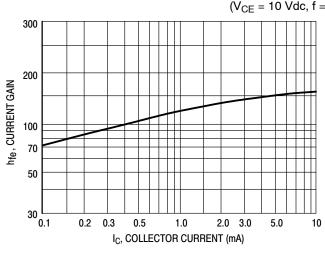


Figure 9.

Figure 10.

h PARAMETERS



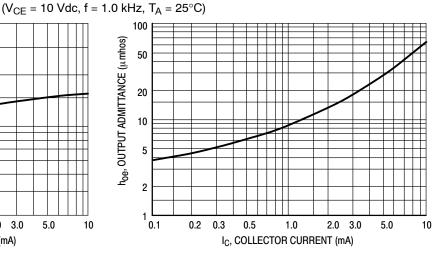
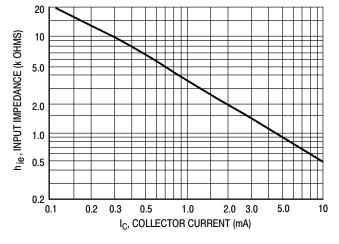


Figure 11. Current Gain

Figure 12. Output Admittance



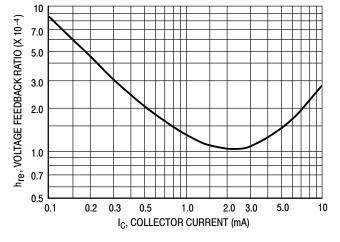


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

2N3903, 2N3904

TYPICAL STATIC CHARACTERISTICS

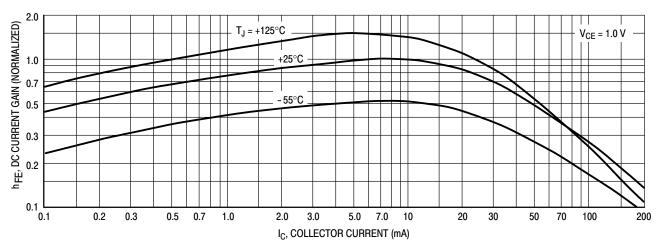


Figure 15. DC Current Gain

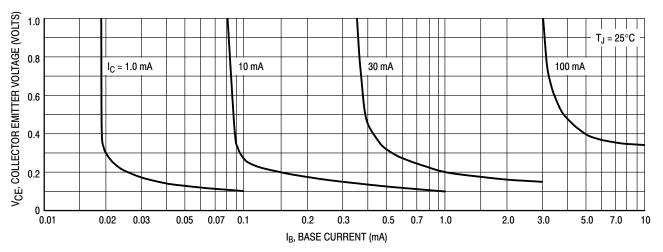


Figure 16. Collector Saturation Region

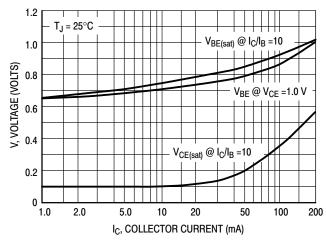


Figure 17. "ON" Voltages

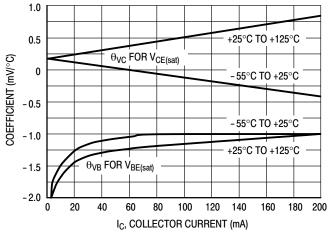
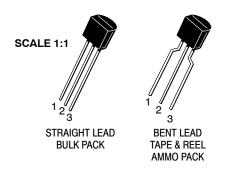
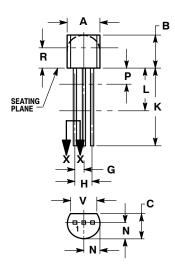


Figure 18. Temperature Coefficients



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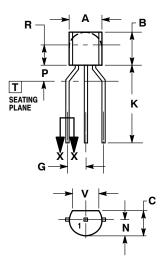


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS				
DIM	MIN	MAX			
Α	4.45	5.20			
В	4.32	5.33			
С	3.18	4.19			
D	0.40	0.54			
G	2.40	2.80			
J	0.39	0.50			
K	12.70				
N	2.04	2.66			
P	1.50	4.00			
R	2.93				
٧	3.43				

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

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DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE ANODE
2. 3.	CATHODE & ANODE CATHODE	2. 3.	GATE MAIN TERMINAL 2	2. 3.		2. 3.	COLLECTOR BASE	2. 3.	CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
2.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	PIN 1	EMITTER COLLECTOR/ANODE CATHODE	PIN 1	MT 1
	V _{CC} GROUND 2 OUTPUT								
STYLE 31: PIN 1. 2. 3.	GATE DRAIN SOURCE	STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN INPUT OUTPUT	STYLE 34: PIN 1. 2. 3.	INPUT GROUND LOGIC	STYLE 35: PIN 1. 2. 3.	GATE COLLECTOR EMITTER

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